



It combines 511(t)25(r)-7(e)11(n)-11(c)23(h)-11(51M(r)-

T_c =25

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _{D@TC=25}	-120	A
	I _{D@TC=75}	-91	A
	I _{D@TC=100}	-75	A
Pulsed Drain Current	I _{DM}	-360	A
Total Power Dissipation(TC=25)	P _{D@TC=25}	125	W
Total Power Dissipation(TA=25)	P _{D@TA=25}	5	W
Operating Junction Temperature	T _J	-55 to 150	
Storage Temperature	T _{STG}	-55 to 150	
Single Pulse Avalanche Energy	E _{AS}	180	mJ
Avalanche Current	I _{AS}	60	A



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1	° C/W

Fig.1 Gate-Charge Characteristics

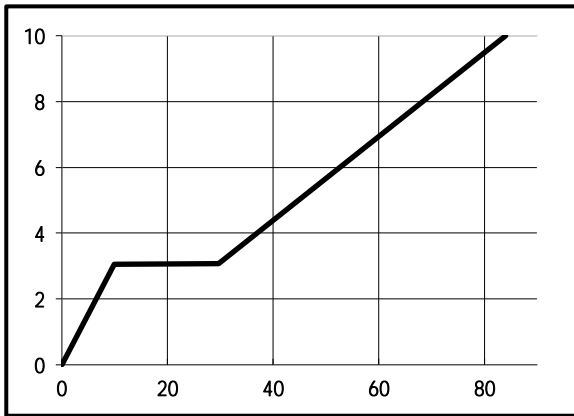


Fig.2 Capacitance Characteristics

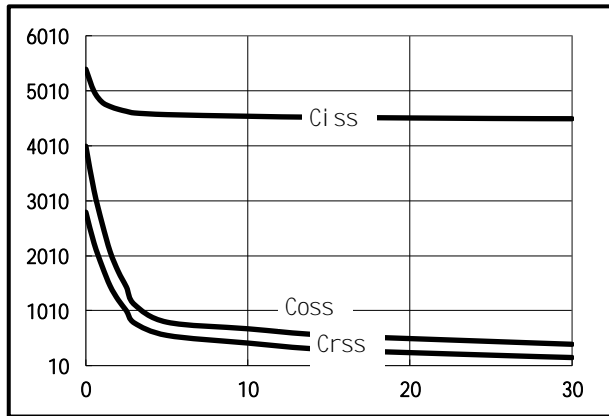


Fig.3 Power Dissipation

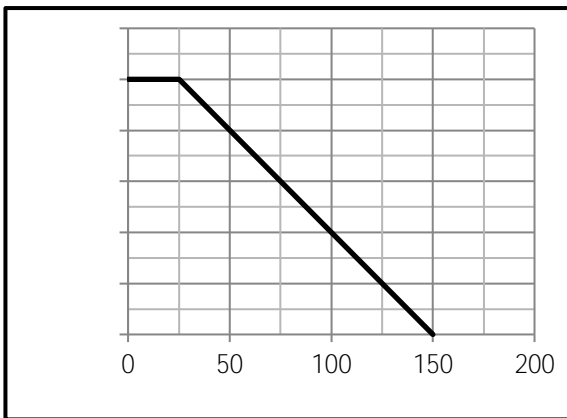


Fig.4 Typical output Characteristics

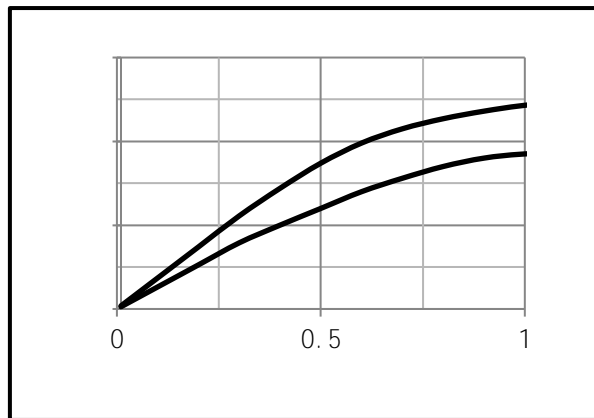


Fig.5 Threshold Voltage V.S Junction Temperature

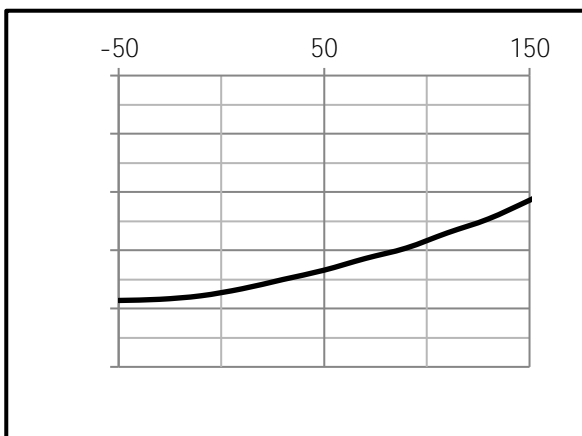
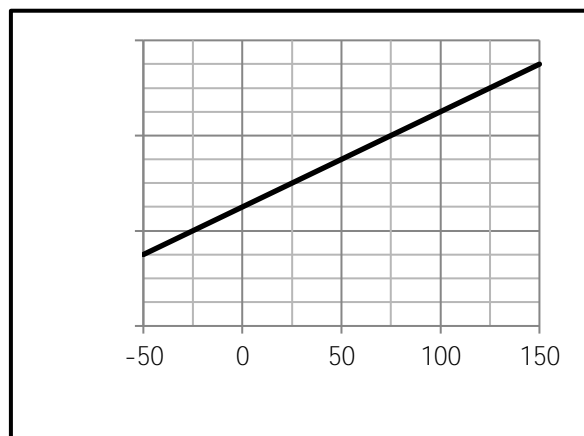


Fig.6 Resistance V.S Drain Current



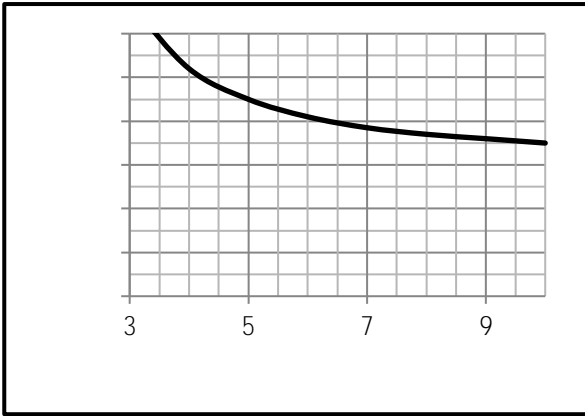


Fig.9 Switching Time Measurement Circuit

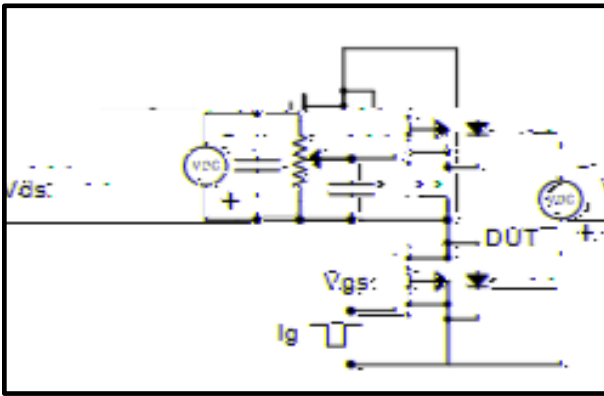


Fig.11 Switching Time Measurement Circuit

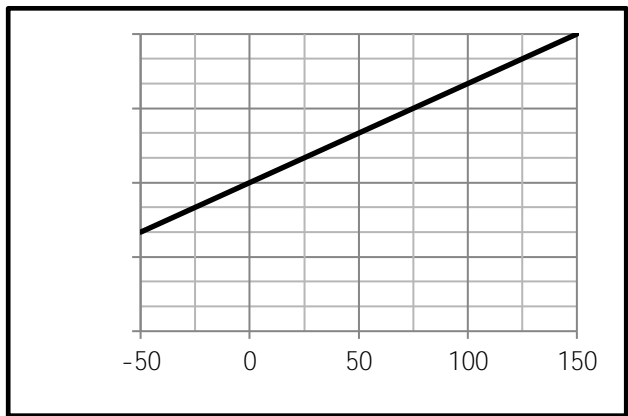
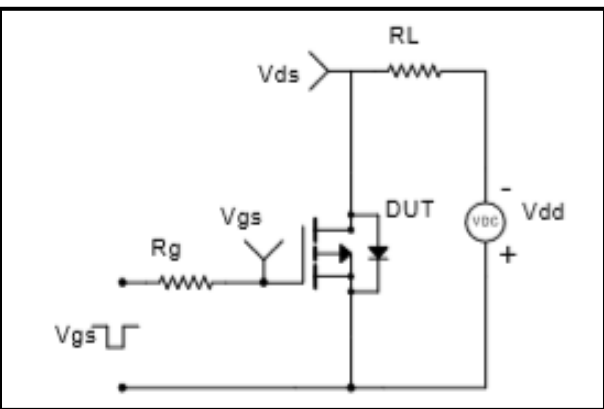


Fig.10 Gate Charge Waveform

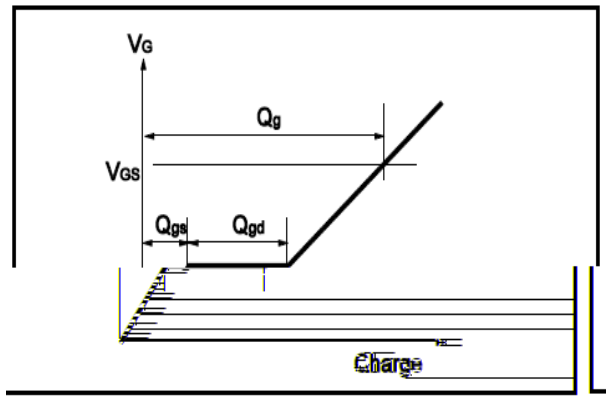
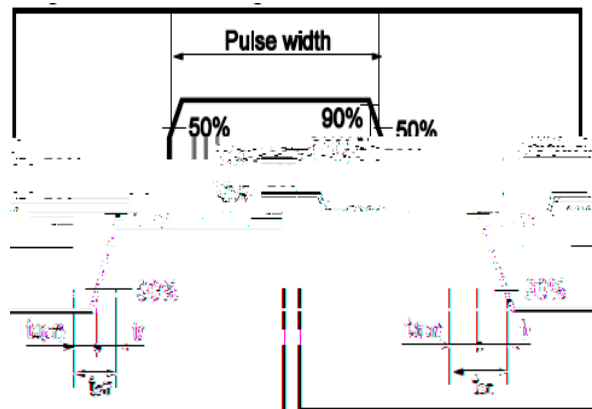


Fig.12 Gate Charge Waveform





(TO-263)

Unit mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25 1.25